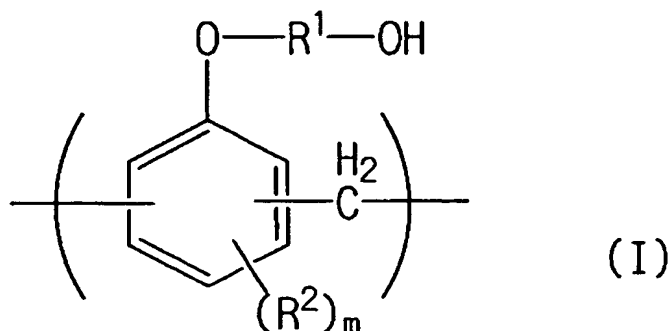
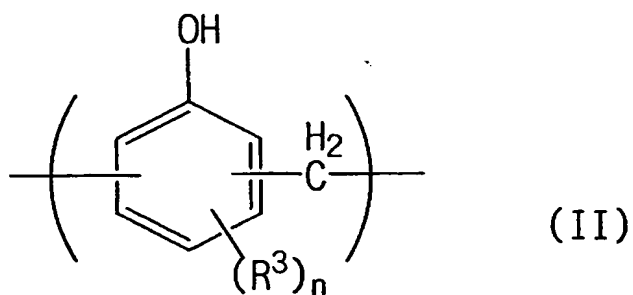


## CLAIMS

1. A positive photoresist composition comprising an alkali-soluble novolak resin (A) containing a structural unit (a1) represented by a general formula (I) shown below:

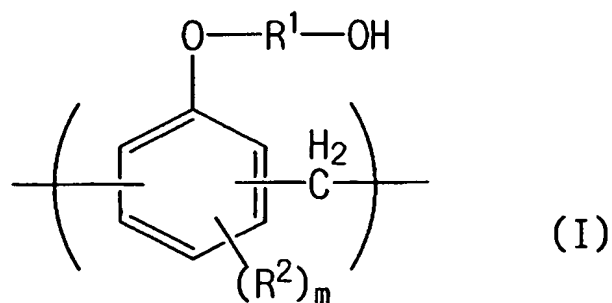


[wherein,  $\text{R}^1$  represents an alkylene group of 1 to 5 carbon atoms,  $\text{R}^2$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $m$  represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:

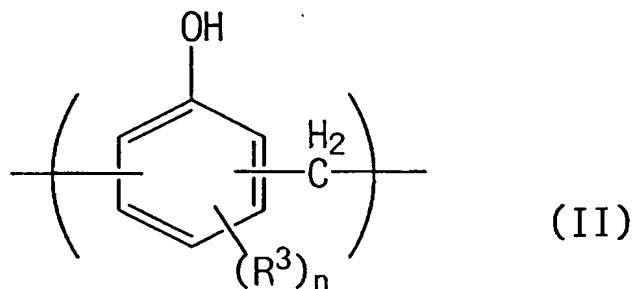


[wherein,  $\text{R}^3$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $n$  represents an integer of 1 to 3], and a photosensitizer (B).

2. A positive photoresist composition comprising an alkali-soluble novolak resin (A') containing a structural unit (a1) represented by a general formula (I) shown below:



[wherein,  $R^1$  represents an alkylene group of 1 to 5 carbon atoms,  $R^2$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $m$  represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:



[wherein,  $R^3$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $n$  represents an integer of 1 to 3], wherein a portion of hydrogen atoms of said hydroxyl groups contained within said resin are substituted with 1,2-naphthoquinonediazidesulfonyl groups.

3. A positive photoresist composition according to claim 2, further comprising a photosensitizer (B).
4. A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 3 to a substrate,

conducting a prebake, performing selective exposure, and then performing alkali developing to form the resist pattern.